AMENDMENTS

In the Claims:

Please cancel claims 23-31 and add new claim 32. Please amend claims 1, 4-8, 10-18, and 20-22, as indicated in the attached **Version With Markings to Show Changes Made**. The complete set of pending claims, in amended form, is as follows:

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1. (Amended) A method for forming a semiconductor product, comprising:

providing a semiconductor substrate having an insulating layer formed thereover and including a top surface;

providing a substructure having a bottom portion formed of a dielectric film;

bonding said bottom portion of said substructure to said top surface of said substrate; and

forming isolated silicon sections, each bonded subjacently by horizontal sections of a conductive material and laterally by vertical sections of said conductive material, in a top portion of said substructure.

2. The method as in claim 1, further comprising forming semiconductor devices at least one of in and on said isolated silicon sections.

3. The method as in claim 2, wherein said semiconductor devices formed in a first plurality of said isolated silicon sections combine to form an integrated circuit.

4. (Amended) The method as in claim 3, further comprising enclosing a group of said first plurality of isolated silicon sections with conductive materials.

5. (Amended) The method as in claim 4, in which said enclosing includes forming insulating materials over said group of isolated silicon sections, forming a conductive cover layer over said insulating materials and forming side conductive materials

extending from said conductive cover layer to said vertical sections which peripherally surround said group,

said conductive material, said conductive cover layer and said side conductive materials combining to electromagnetically shield said group.

6. (Amended) The method as in claim 1, further comprising enclosing at least some of said individual isolated silicon sections with conductive material.

7. (Amended) The method as in claim 6, in which said enclosing includes, for ~~each isolated silicon section being enclosed, forming insulating materials over said isolated~~ silicon section, forming a conductive cover layer over said insulating materials and forming side conductive materials extending from said conductive cover layer to said vertical sections which bound said isolated silicon section;

said conductive material, said conductive cover layer and said side conductive materials combining to electromagnetically shield said isolated silicon section.

8. (Amended) The method as in claim 7, in which said forming insulating materials includes, for each isolated silicon section being enclosed, forming a succession of insulating layers and forming trenches in each of said succession of insulating layers, said trenches extending along the periphery of said isolated silicon section, and filling said trenches with said side conductive materials.

9. The method as in claim 7, in which said horizontal sections of conductive material, said vertical sections of said conductive material, said conductive cover layer and said side conductive materials are each formed of tungsten.

10. (Amended) The method as in claim 7, in which said forming insulating materials includes, for each isolated silicon section being enclosed, forming a succession of insulating layers and said enclosing includes forming one of a continuous opening and a

linear array of spaced openings in each of said succession of insulating layers above said vertical sections which bound said isolated silicon section, and filling said formed corresponding openings with said side conductive materials.

11. (Amended) The method as in claim 1, in which said semiconductor substrate and said substructure each include about the same lateral dimensions and shape.

12. (Amended) The method as in claim 1, in which said providing a substructure includes providing a further substrate having said substructure formed as a portion thereof and further comprising separating said substructure from other portions of said further substrate.

13. (Amended) The method as in claim 12, in which said separating takes place after said bonding.

14. (Amended) The method as in claim 12, in which said separating comprises one of backgrinding and etching.

15. (Amended) The method as in claim 12, in which said providing a substructure includes providing said further substrate having a top surface, implanting hydrogen into an upper region of said further substrate, said upper region including a subjacent boundary, forming trenches within said upper region and extending vertically downward from said top surface, forming said conductive material over said top surface and filling said trenches, and forming said dielectric film over said conductive material thereby forming said substructure in overturned position as a top portion of said further substrate, and

said separating includes separating said substructure from other portions of said further substrate along a crack propagated along said subjacent boundary.

16. (Amended) The method as in claim 15 in which said separating includes heating to a temperature within the range of 400°C to 600°C.

17. (Amended) The method as in claim 15, further comprising planarizing after said forming said conductive material over said top surface of said further substrate and filling said trenches, and prior to said forming said dielectric film.

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18. (Amended) The method as in claim 1, in which said bonding comprises hydrophilic bonding.

19. The method as in claim 1, wherein said vertical sections of said conductive material and said horizontal sections of said conductive material each comprise tungsten.

20. (Amended) The method as in claim 1, wherein said insulating layer comprises a silicon dioxide layer and said dielectric film comprises a silicon dioxide film and said bonding includes hydrophilic bonding

21. (Amended) The method as in claim 5, in which said side conductive materials are not continuous and include openings that extend through said side conductive materials, and further comprising forming interconnect leads extending through said openings.

22. (Amended) The method as in claim 7, in which said side conductive materials are not continuous and include openings that extend through said side conductive materials, and further comprising forming interconnect leads extending through said openings.